Absolute Maximum Ratings

Stresses beyond the limits listed below may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

V _S	0V to +14V
V _{IN} V _S - 0.5V to	+V _S +0.5V

Operating Conditions

Supply Voltage Range	2.7 to 12.6V
Operating Temperature Range	40°C to 125°C
Junction Temperature	150°C
Storage Temperature Range	65°C to 150°C
Lead Temperature (Soldering, 10s)	260°C

Package Thermal Resistance

θ _{JA} (TSOT23-5)	215°C/W
θ _{JA} (SOIC-8)	150°C/W
θ _{JA} (MSOP-8)	200°C/W
θ _{JA} (SOIC-14)	90°C/W
θ _{JA} (TSSOP-14)	100°C/W
Package thermal resistance (θ ₁ Λ). JEDEC st	tandard, multi-laver

Package thermal resistance (θ_{JA}), JEDEC standard, multi-layer test boards, still air.

ESD Protection

TSOT-5 (HBM)	1kV
SOIC-8 (HBM)	1kV
TSOT-5 (CDM)	2kV
SOIC-8 (CDM)	2kV

ESD Rating for HBM (Human Body Model) and CDM (Charged Device Model).

Electrical Characteristics at +3V

 T_A = 25°C, V_S = +3V, R_f = 1.5k $\Omega,~R_L$ = 2k Ω to $V_S/2;~G$ = 2; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency	Domain Response					
GBWP	-3dB Gain Bandwidth Product	$G = +11, V_{OUT} = 0.2V_{pp}$		90		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.2V_{pp}, R_F = 0$		245		MHz
BW _{SS}	-3dB Bandwidth	$V_{OUT} = 0.2V_{pp}$		85		MHz
f _{0.1dB}	0.1dB Gain Flatness	$V_{OUT} = 0.2V_{pp}, R_L = 150\Omega$		16		MHz
BW _{LS}	Large Signal Bandwidth	$V_{OUT} = 2V_{pp}$		55		MHz
DG	Differential Gain	DC-coupled Output		0.03		%
DG	Dillerential Gain	AC-coupled Output		0.04		%
DP	Differential Phase	DC-coupled Output		0.03		۰
DF	Dillereritiai Friase	AC-coupled Output		0.06		٥
Time Doma	ain					
t_R , t_F	Rise and Fall Time	V _{OUT} = 0.2V step; (10% to 90%)		5		ns
t _S	Settling Time to 0.1%	V _{OUT} = 1V step		25		ns
OS	Overshoot	V _{OUT} = 0.2V step		8		%
SR	Slew Rate	G = -1, 2V step		175		V/µs
Distortion/I	Noise Response					
THD	Total Harmonic Distortion	$1MHz$, $V_{OUT} = 1V_{pp}$		75		dBc
e _n	Input Voltage Noise	>50kHz		16		nV/ √ Hz
X _{TALK}	Crosstalk	f = 5MHz		58		dB
DC Perform	nance					
V_{IO}	Input Offset Voltage			0.5		mV
d_{VIO}	Average Drift			5		μV/°C
I_{B}	Input Bias Current			1.4		μA
dI_B	Average Drift			2		nA/°C
Ios	Input Offset Current			0.05		μA
PSRR	Power Supply Rejection Ratio	DC		102		dB
A _{OL}	Open Loop Gain	$R_L = 2k\Omega$		92		dB
I _S	Supply Current	per channel		2.6		mA
Input Char	acteristics					
C _{IN}	Input Capacitance			0.5		pF
CMIR	Common Mode Input Range			-0.3 to 2.1		V
CMRR	Common Mode Rejection Ratio	DC, V _{CM} = 0 to 1.5V		100		dB
Output Cha	aracteristics					
V	Outside Code	R _L = 150Ω		0.3 to 2.75		V
V _{OUT}	Output Swing	$R_L = 2k\Omega$		0.02 to 2.96		V
I _{OUT}	Output Current			±100		mA
I _{SC}	Short Circuit Current	$V_{OUT} = V_S/2$		±125		V
V _S	Power Supply Operating Range			2.7 to 12.6		V

Electrical Characteristics at +5V

 T_A = 25°C, V_S = +5V, R_f = 1.5k $\Omega,~R_L$ = 2k Ω to $V_S/2;~G$ = 2; unless otherwise noted.

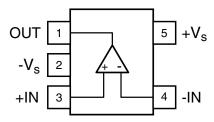
Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency	Domain Response					
GBWP	-3dB Gain Bandwidth Product	$G = +11, V_{OUT} = 0.2V_{pp}$		95		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.2V_{pp}, R_F = 0$		250		MHz
BW _{SS}	-3dB Bandwidth	$V_{OUT} = 0.2V_{pp}$		85		MHz
f _{0.1dB}	0.1dB Gain Flatness	$V_{OUT} = 0.2V_{pp}, R_L = 150\Omega$		35		MHz
BW _{LS}	Large Signal Bandwidth	$V_{OUT} = 2V_{pp}$		65		MHz
DG	Differential Gain	DC-coupled Output		0.03		%
DG	Differential Gain	AC-coupled Output		0.04		%
DP	Differential Phase	DC-coupled Output		0.03		٥
DF	Differential Friase	AC-coupled Output		0.06		0
Time Doma	ain					
t_R , t_F	Rise and Fall Time	V _{OUT} = 0.2V step		5		ns
t _S	Settling Time to 0.1%	V _{OUT} = 2V step		25		ns
OS	Overshoot	V _{OUT} = 0.2V step		5		%
SR	Slew Rate	G = -1, 4V step		220		V/µs
Distortion/I	Noise Response			_		
THD	Total Harmonic Distortion	1MHz, $V_{OUT} = 2V_{pp}$		-75		dBc
e _n	Input Voltage Noise	>50kHz		16		nV/ √ Hz
X _{TALK}	Crosstalk	f = 5MHz		58		dB
DC Perforr	mance					
V_{IO}	Input Offset Voltage		-7	0.5	7	mV
d_{VIO}	Average Drift			5		μV/°C
I_{B}	Input Bias Current		-2	1.4	2	μA
dI_B	Average Drift			2		nA/°C
Ios	Input Offset Current		-0.75	0.05	0.75	μA
PSRR	Power Supply Rejection Ratio	DC	80	102		dB
A _{OL}	Open Loop Gain	$R_L = 2k\Omega$	80	92		dB
I _S	Supply Current	per channel		2.6	4	mA
Input Char	acteristics					
C _{IN}	Input Capacitance			0.5		pF
CMIR	Common Mode Input Range			-0.3 to 4.1		V
CMRR	Common Mode Rejection Ratio	DC, V _{CM} = 0 to 3.5V	75	100		dB
Output Cha	aracteristics		'	,	'	·
V	Outsid Outside	R _L = 150Ω	0.35	0.1 to 4.9	4.65	V
V _{OUT}	Output Swing	$R_L = 2k\Omega$		0.03 to 4.95		V
I _{OUT}	Output Current			±100		mA
I _{SC}	Short Circuit Current	V _{OUT} = V _S / 2		±125		V
V _S	Power Supply Operating Range			2.7 to 12.6		V

Electrical Characteristics at ±5V

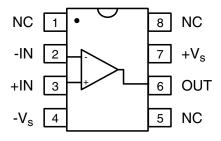
 T_A = 25°C, V_S = ±5V, R_f = 1.5k $\Omega,~R_L$ = 2k Ω to GND; G = 2; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency	Domain Response					
GBWP	-3dB Gain Bandwidth Product	$G = +11, V_{OUT} = 0.2V_{pp}$		90		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.2V_{pp}, R_F = 0$		260		MHz
BW _{SS}	-3dB Bandwidth	$V_{OUT} = 0.2V_{pp}$		85		MHz
f _{0.1dB}	0.1dB Gain Flatness	$V_{OUT} = 0.2V_{pp}, R_L = 150\Omega$		22		MHz
BW _{LS}	Large Signal Bandwidth	V _{OUT} = 2V _{pp}		65		MHz
DG	Differential Gain	DC-coupled Output		0.03		%
DG	Differential Gain	AC-coupled Output		0.04		%
DP	Differential Phase	DC-coupled Output		0.03		0
DF	Dillererillar Friase	AC-coupled Output		0.06		0
Time Doma	ain					
t_R , t_F	Rise and Fall Time	V _{OUT} = 0.2V step		5		ns
t _S	Settling Time to 0.1%	$V_{OUT} = 2V$ step, $R_L = 100\Omega$		25		ns
OS	Overshoot	V _{OUT} = 0.2V step		5		%
SR	Slew Rate	G = -1, 5V step		225		V/µs
Distortion/I	Noise Response					
THD	Total Harmonic Distortion	$1MHz$, $V_{OUT} = 2V_{pp}$		76		dBc
e _n	Input Voltage Noise	>50kHz		16		nV/√Hz
X _{TALK}	Crosstalk	f = 5MHz		58		dB
DC Perform	nance					
V_{IO}	Input Offset Voltage			0.5		mV
d_{VIO}	Average Drift			5		μV/°C
I_{B}	Input Bias Current			1.3		μA
dI_B	Average Drift			2		nA/°C
Ios	Input Offset Current			0.04		μA
PSRR	Power Supply Rejection Ratio	DC		102		dB
A _{OL}	Open Loop Gain	$R_L = 2k\Omega$		92		dB
I _S	Supply Current	per channel		2.6		mA
Input Char	acteristics					
C _{IN}	Input Capacitance			0.5		pF
CMIR	Common Mode Input Range			-5.3 to 4.1		V
CMRR	Common Mode Rejection Ratio	DC, V _{CM} = -5 to 3.5V		100		dB
Output Cha	aracteristics		<u>'</u>	,	'	<u>'</u>
V	Outro t Surian	R _L = 150Ω		-4.8 to 4.8		V
V _{OUT}	Output Swing	$R_L = 2k\Omega$		-4.95 to 4.93		V
I _{OUT}	Output Current			±100		mA
I _{SC}	Short Circuit Current	$V_{OUT} = V_S/2$		±125		V
Vs	Power Supply Operating Range			2.7 to 12.6		V

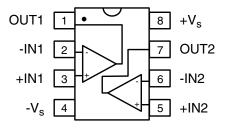
CLC1007 Pin Configurations TSOT-5



SOIC-8



CLC2007 Pin Configuration SOIC-8 / MSOP-8



CLC1007 Pin Assignments

TSOT-5

Pin No.	Pin Name	Description
1	OUT	Output
2	-V _S	Negative supply
3	+IN	Positive input
4	-IN	Negative input
5	+V _S	Positive supply

SOIC-8

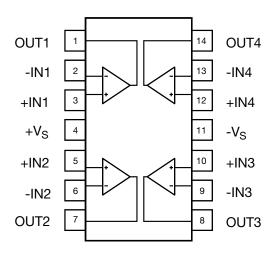
Pin No.	Pin Name	Description
1	NC	No Connect
2	-IN	Negative input
3	+IN	Positive input
4	-V _S	Negative supply
5	NC	No Connect
6	OUT	Output
7	+V _S	Positive supply
8	NC	No Connect

CLC2007 Pin Assignments

SOIC-8 / MSOP-8

Pin No.	Pin Name	Description	
1	OUT1	Output, channel 1	
2	-IN1	Negative input, channel 1	
3	+IN1	Positive input, channel 1	
4	-V _S	Negative supply	
5	+IN2	Positive input, channel 2	
6	-IN2	Negative input, channel 2	
7	OUT2	Output, channel 2	
8	+V _S	Positive supply	

CLC4007 Pin Configuration SOIC-14 / TSSOP-14



CLC4007 Pin Assignments

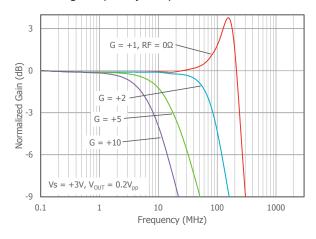
SOIC-14 / TSSOP-14

Pin No.	Pin Name	Description
1	OUT1	Output, channel 1
2	-IN1	Negative input, channel 1
3	+IN1	Positive input, channel 1
4	+V _S	Positive supply
5	+IN2	Positive input, channel 2
6	-IN2	Negative input, channel 2
7	OUT2	Output, channel 2
8	OUT3	Output, channel 3
9	-IN3	Negative input, channel 3
10	+IN3	Positive input, channel 3
11	-V _S	Negative supply
12	+IN4	Positive input, channel 4
13	-IN4	Negative input, channel 4
14	OUT4	Output, channel 4

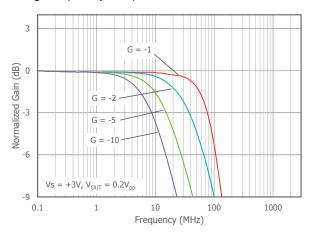
Typical Performance Characteristics at +3V

 $T_A = 25$ °C, $V_S = +3V$, $R_L = 2k\Omega$ to $V_S/2$, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

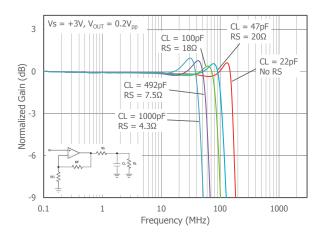
Non-Inverting Frequency Response



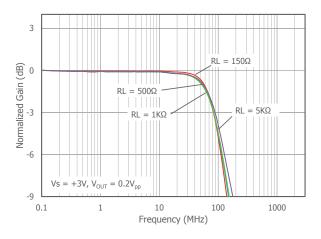
Inverting Frequency Response



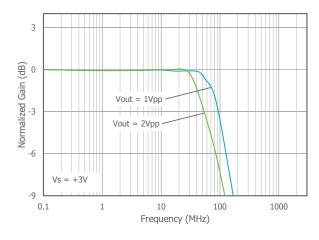
Frequency Response vs C_L



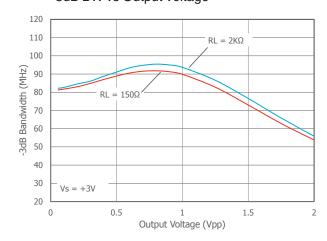
Frequency Response vs R_I



Large Signal Frequency Response



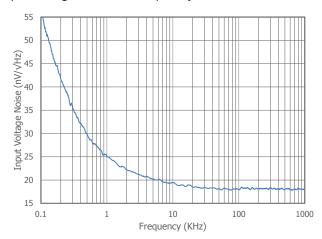
-3dB BW vs Output Voltage



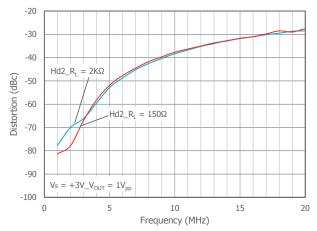
Typical Performance Characteristics at +3V

 T_A = 25°C, V_S = +3V, R_L = 2k Ω to $V_S/2,~G$ = +2, R_F = 1.5k Ω ; unless otherwise noted.

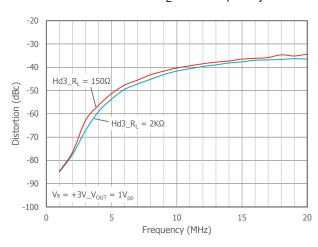
Input Voltage Noise vs Frequency



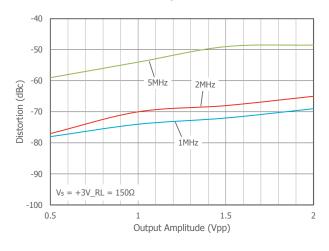
2nd Harmonic Distortion vs $R_{L}\,\mbox{over}$ Frequency



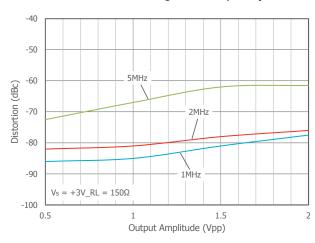
3rd Harmonic Distortion vs R_L over Frequency



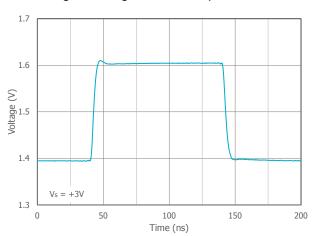
2nd Harmonic Distortion vs VO over Frequency



3rd Harmonic Distortion vs VO over Frequency



Non-Inverting Small Signal Pulse Response

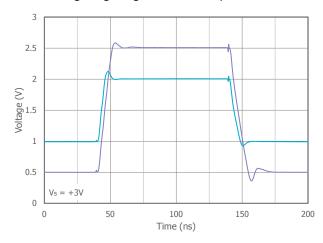


Rev 1D.R

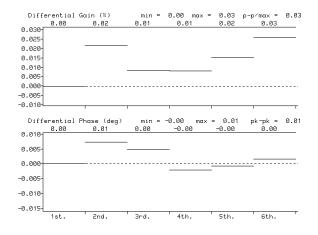
Typical Performance Characteristics at +3V

 $T_A = 25$ °C, $V_S = +3V$, $R_L = 2k\Omega$ to $V_S/2$, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

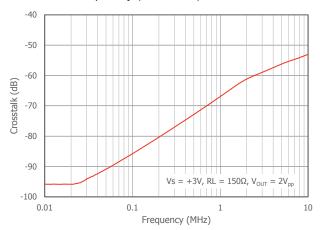
Non-Inverting Large Signal Pulse Response



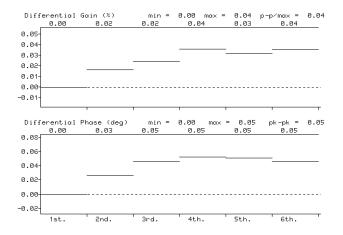
Differential Gain & Phase_DC Coupled



Crosstalk vs Frequency (CLC2007)



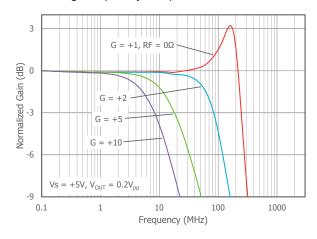
Differential Gain & Phase_AC Coupled



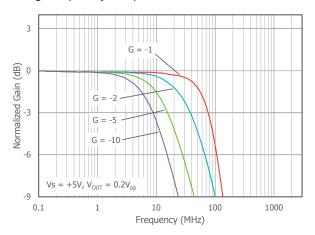
Typical Performance Characteristics at +5V

 $T_A = 25$ °C, $V_S = +5V$, $R_L = 2k\Omega$ to $V_S/2$, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

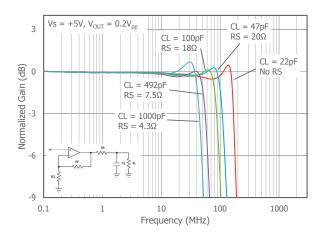
Non-Inverting Frequency Response



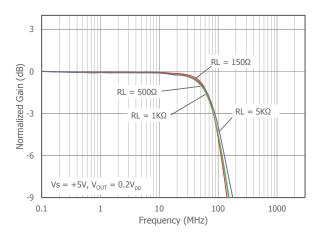
Inverting Frequency Response



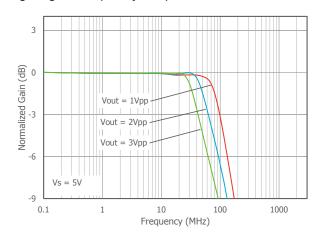
Frequency Response vs C_L



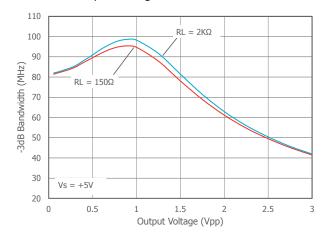
Frequency Response vs R_I



Large Signal Frequency Response



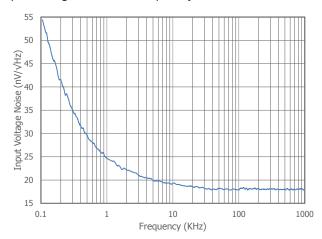
-3dB BW vs Output Voltage



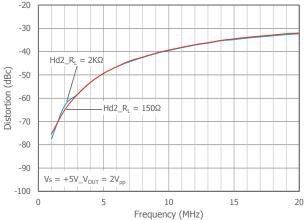
Typical Performance Characteristics at +5V

 T_A = 25°C, V_S = +5V, R_L = 2k Ω to $V_S/2,~G$ = +2, R_F = 1.5k Ω ; unless otherwise noted.

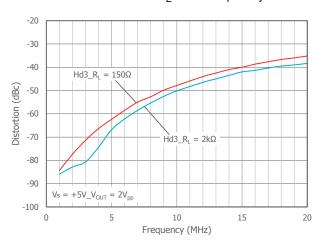
Input Voltage Noise vs Frequency



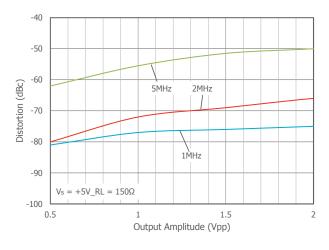
2nd Harmonic Distortion vs R_L over Frequency



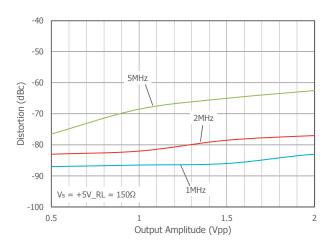
3rd Harmonic Distortion vs R_L over Frequency



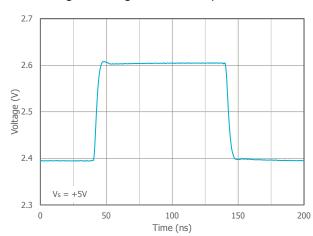
2nd Harmonic Distortion vs VO over Frequency



3rd Harmonic Distortion vs VO over Frequency



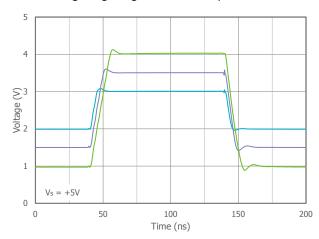
Non-Inverting Small Signal Pulse Response



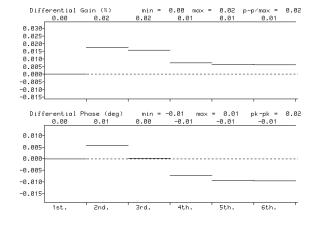
Typical Performance Characteristics at +5V

 $T_A = 25$ °C, $V_S = +5V$, $R_L = 2k\Omega$ to $V_S/2$, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

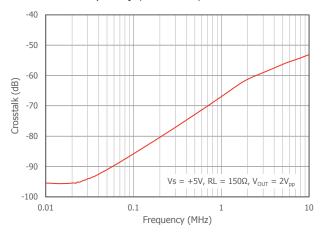
Non-Inverting Large Signal Pulse Response



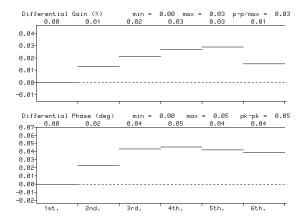
Differential Gain & Phase_DC Coupled



Crosstalk vs Frequency (CLC2007)



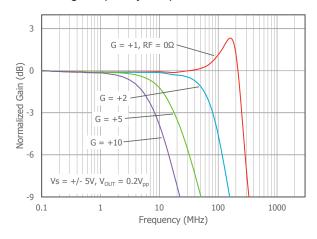
Differential Gain & Phase_AC Coupled



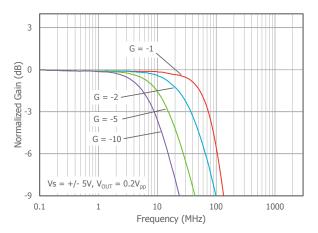
Typical Performance Characteristics at ±5V

 $T_A = 25$ °C, $V_S = \pm 5V$, $R_L = 2k\Omega$ to GND, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

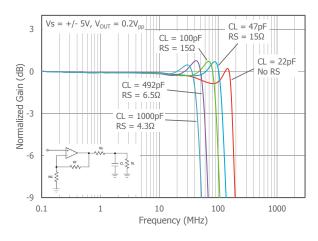
Non-Inverting Frequency Response



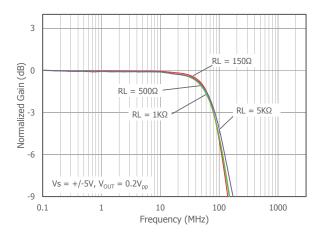
Inverting Frequency Response



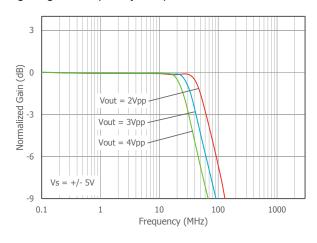
Frequency Response vs C_L



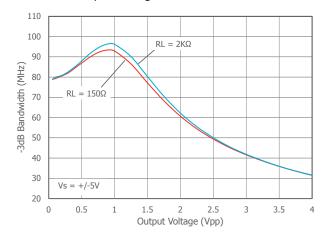
Frequency Response vs R_I



Large Signal Frequency Response



-3dB BW vs Output Voltage

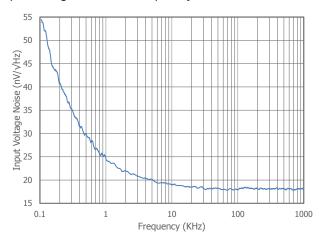


Rev 1D.R

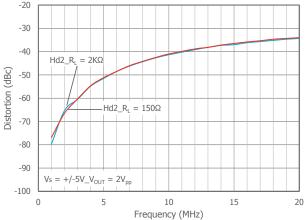
Typical Performance Characteristics at ±5V

 T_A = 25°C, V_S = ±5V, R_L = 2k Ω to GND, G = +2, R_F = 1.5k Ω ; unless otherwise noted.

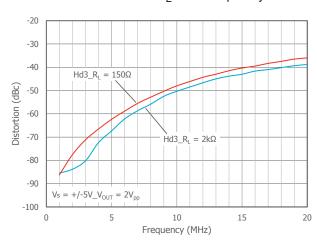
Input Voltage Noise vs Frequency



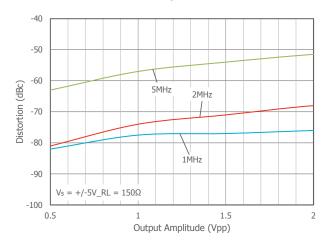
2nd Harmonic Distortion vs R_L over Frequency



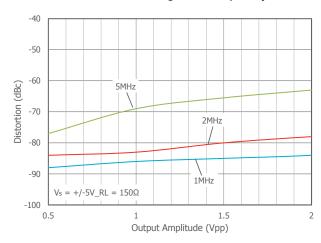
3rd Harmonic Distortion vs R_L over Frequency



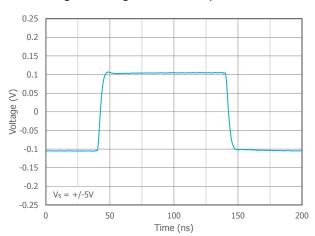
2nd Harmonic Distortion vs VO over Frequency



3rd Harmonic Distortion vs VO over Frequency



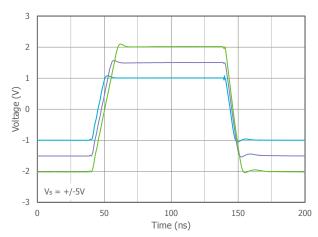
Non-Inverting Small Signal Pulse Response



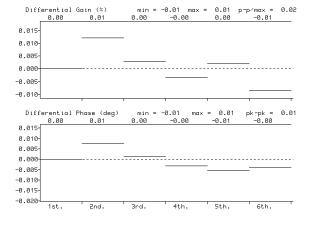
Typical Performance Characteristics at ±5V

 $T_A = 25$ °C, $V_S = \pm 5$ V, $R_L = 2k\Omega$ to GND, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

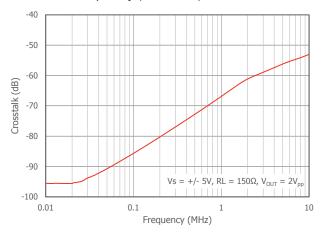
Non-Inverting Large Signal Pulse Response



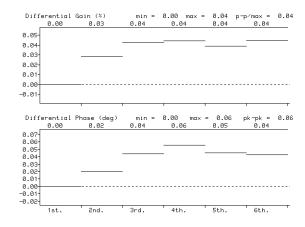
Differential Gain & Phase_DC Coupled



Crosstalk vs Frequency (CLC2007)



Differential Gain & Phase_AC Coupled



Application Information

General Description

The CLC1007, CLC2007, and CLC4007 are single supply, general purpose, voltage-feedback amplifiers fabricated on a complementary bipolar process using a patent pending topography. They feature a rail-to-rail output stage and is unity gain stable. Both gain bandwidth and slew rate are insensitive to temperature.

The common mode input range extends to 300mV below ground and to 0.9V below V_s . Exceeding these values will not cause phase reversal. However, if the input voltage exceeds the rails by more than 0.5V, the input ESD devices will begin to conduct. The output will stay at the rail during this overdrive condition.

The design is short circuit protected and offers "soft" saturation protection that improves recovery time.

Figures 1, 2, and 3 illustrate typical circuit configurations for non-inverting, inverting, and unity gain topologies for dual supply applications. They show the recommended bypass capacitor values and overall closed loop gain equations. Figure 4 shows the typical non-inverting gain circuit for single supply applications.

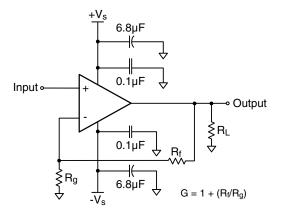


Figure 1: Typical Non-Inverting Gain Circuit

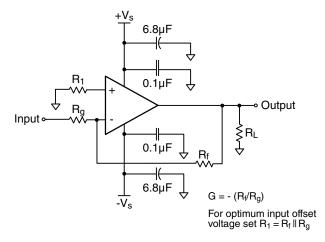


Figure 2: Typical Inverting Gain Circuit

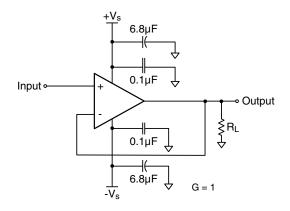


Figure 3: Unity Gain Circuit

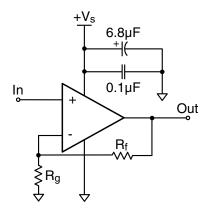


Figure 4: Single Supply Non-Inverting Gain Circuit

Overdrive Recovery

For an amplifier, an overdrive condition occurs when the output and/or input ranges are exceeded. The recovery time varies based on whether the input or output is overdriven and by how much the ranges are exceeded. The CLC1007, CLC2007, and CLC4007 will typically recover in less than 20ns from an overdrive condition. Figure 5 shows the CLC2007 in an overdriven condition.

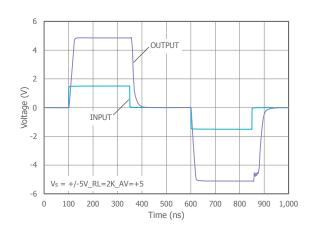


Figure 5: Overdrive Recovery

Power Dissipation

Power dissipation should not be a factor when operating under the stated $2k\Omega$ load condition. However, applications with low impedance, DC coupled loads should be analyzed to ensure that maximum allowed junction temperature is not exceeded. Guidelines listed below can be used to verify that the particular application will not cause the device to operate beyond it's intended operating range.

Maximum power levels are set by the absolute maximum junction rating of 170°C. To calculate the junction temperature, the package thermal resistance value Theta $_{JA}$ (θ_{JA}) is used along with the total die power dissipation.

$$T_{Junction} = T_{Ambient} + (\theta_{JA} \times P_D)$$

Where T_{Ambient} is the temperature of the working environment.

In order to determine P_D , the power dissipated in the load needs to be subtracted from the total power delivered by the supplies.

$$P_D = P_{supply} - P_{load}$$

Supply power is calculated by the standard power equation.

$$P_{\text{supply}} = V_{\text{supply}} \times I_{\text{RMSsupply}}$$
 $V_{\text{supply}} = V_{\text{S+}} - V_{\text{S-}}$

Power delivered to a purely resistive load is:

$$P_{load} = ((V_{load})_{RMS^2})/Rload_{eff}$$

The effective load resistor (Rload_{eff}) will need to include the effect of the feedback network. For instance,

Rload_{eff} in Figure 3 would be calculated as:

$$R_L \parallel (R_f + R_a)$$

These measurements are basic and are relatively easy to perform with standard lab equipment. For design purposes however, prior knowledge of actual signal levels and load impedance is needed to determine the dissipated power. Here, $P_{\rm D}$ can be found from

$$P_D = P_{Ouiescent} + P_{Dynamic} - P_{load}$$

Quiescent power can be derived from the specified I_S values along with known supply voltage, V_{supply} . Load power can be calculated as above with the desired signal amplitudes using:

$$(I_{load})_{RMS} = (V_{load})_{RMS} / Rload_{eff}$$

The dynamic power is focused primarily within the output stage driving the load. This value can be calculated as:

$$P_{Dynamic} = (V_{S+} - V_{load})_{RMS} \times (I_{load})_{RMS}$$

Assuming the load is referenced in the middle of the power rails or $V_{\text{supply}}/2$.

The CLC1007 is short circuit protected. However, this may not guarantee that the maximum junction temperature (+150°C) is not exceeded under all conditions. Figure 6 shows the maximum safe power dissipation in the package vs. the ambient temperature for the packages available.

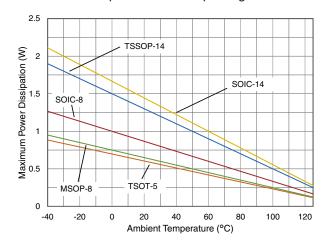


Figure 6. Maximum Power Derating

Driving Capacitive Loads

Increased phase delay at the output due to capacitive loading can cause ringing, peaking in the frequency response, and possible unstable behavior. Use a series resistance, R_S , between the amplifier and the load to help improve stability and settling performance. Refer to Figure 7.

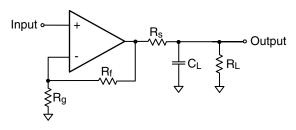


Figure 7. Addition of R_S for Driving Capacitive Loads

Table 1 provides the recommended R_S for various capacitive loads. The recommended R_S values result in approximately <1dB peaking in the frequency response.

C _L (pF)	R _S (Ω)	-3dB BW (MHz)
22pF	0	118
47pF	15	112
100pF	15	91
492pF	6.5	59

Table 1: Recommended R_S vs. C_L

For a given load capacitance, adjust R_S to optimize the tradeoff between settling time and bandwidth. In general, reducing R_S will increase bandwidth at the expense of additional overshoot and ringing.

Layout Considerations

General layout and supply bypassing play major roles in high frequency performance. Resurgent has evaluation boards to use as a guide for high frequency layout and as an aid in device testing and characterization. Follow the steps below as a basis for high frequency layout:

- Include 6.8µF and 0.1µF ceramic capacitors for power supply decoupling
- Place the 6.8µF capacitor within 0.75 inches of the power pin
- Place the 0.1µF capacitor within 0.1 inches of the power pin
- Remove the ground plane under and around the part, especially near the input and output pins to reduce parasitic capacitance
- Minimize all trace lengths to reduce series inductances

Refer to the evaluation board layouts below for more information.

Evaluation Board Information

The following evaluation boards are available to aid in the testing and layout of these devices:

Evaluation Board #	Products
CEB002	CLC1007 in TSOT
CEB003	CLC1007 in SOIC
CEB006	CLC2007 in SOIC
CEB010	CLC2007 in MSOP
CEB018	CLC4007 in SOIC
CEB019	CLC4007 in TSSOP

Evaluation Board Schematics

Evaluation board schematics and layouts are shown in Figures 8-20. These evaluation boards are built for dual-supply operation. Follow these steps to use the board in a single-supply application:

- 1. Short -V_S to ground.
- 2. Use C3 and C4, if the -V_S pin of the amplifier is not directly connected to the ground plane.

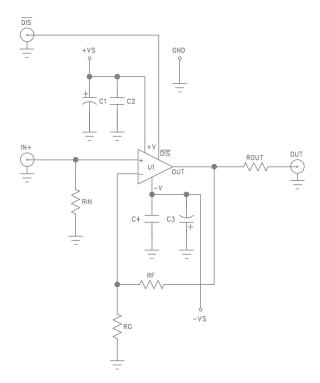


Figure 8. CEB002 & CEB003 Schematic

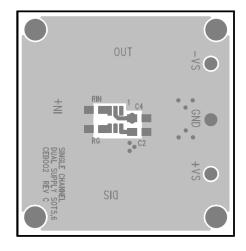


Figure 9. CEB002 Top View

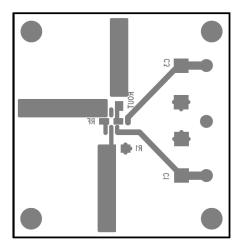


Figure 10. CEB002 Bottom View

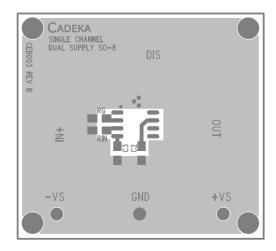


Figure 11. CEB003 Top View

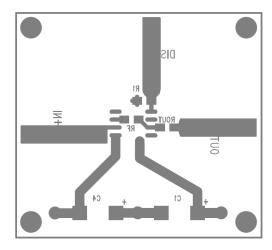


Figure 12. CEB003 Bottom View

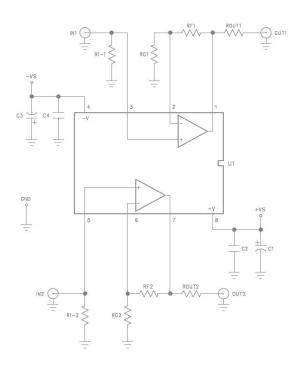


Figure 13. CEB006 & CEB010 Schematic

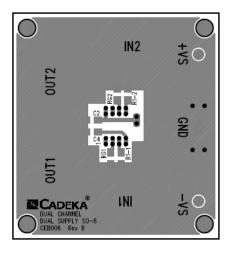


Figure 14. CEB006 Top View

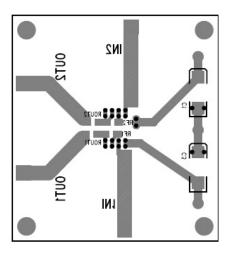


Figure 15. CEB006 Bottom View

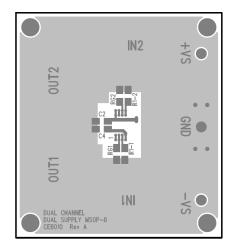


Figure 16. CEB010 Top View

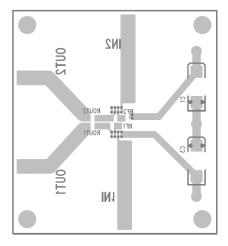


Figure 17. CEB010 Bottom View

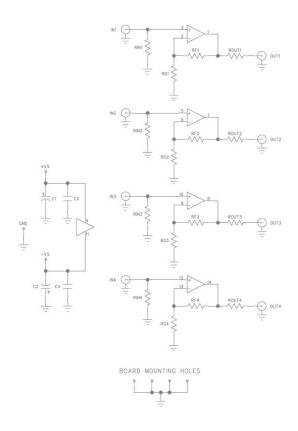


Figure 18. CEB018 Schematic

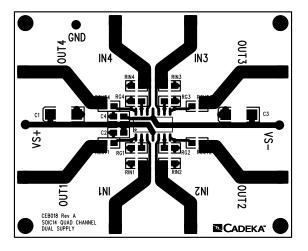


Figure 19. CEB018 Top View

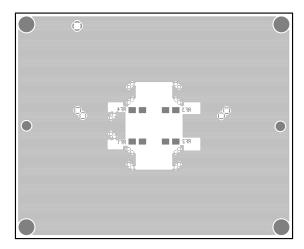
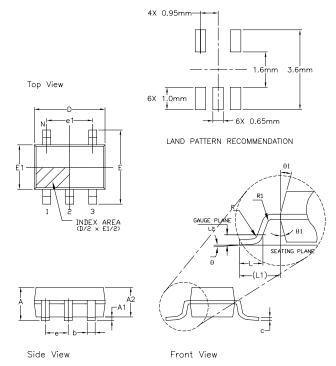


Figure 20. CEB018 Bottom View

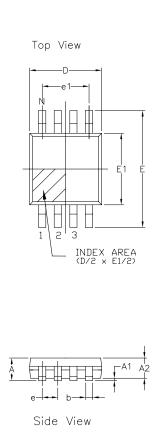
Mechanical Dimensions

TSOT-5 Package

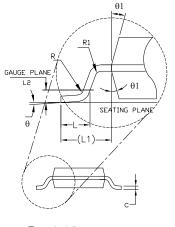


5 Pin TSOT (OPTION 2)						
SYMBOLS	DIMENSION IN MM (Control Unit)			DIMENSION IN INCH (Reference Unit)		
	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.75	_	0.80	0.030	_	0.031
A1	0.00	_	0.05	0.000	_	0.002
A2	0.70	0.75	0.78	0.028	0.030	0.031
b	0.35	_	0.50	0.012	_	0.020
С	0.10	_	0.20	0.003	_	0.008
D	2	2.90 BS	SC .	0.114 BSC		
E	2	2.80 BS	iC .	0.110 BSC		
E1	1	.60 BS	SC .	0.063 BSC		
е	C).95 BS	iC .	0.038 BSC		
e1	1	.90 BS	SC .	0.075 BSC		
L	0.37	0.45	0.60	0.012	0.018	0.024
L1	(0.60 RE	F	0	.024 RE	F
L2	0).25 BS	SC .	0	.010 BS	SC .
R	0.10	_	_	0.004	_	_
R1	0.10	_	0.25	0.004	_	0.010
θ	0.	4'	8,	0,	4*	8,
θ1	4.	10°	12*	4*	10°	12*
N		5			5	

MSOP-8 Package

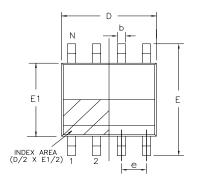


8 Pin	MSOP	JEDEO	MO-	187 V	ariatio	n AA	
SYMBOLS		SIONS ntrol U			DIMENSIONS IN INCH (Reference Unit)		
	MIN	NOM	MAX	MIN	NOM	MAX	
Α	_	_	1.10	_		0.043	
A1	0.00	_	0.15	0.000	-	0.006	
A2	0.75	0.85	0.95	0.030	0.033	0.037	
ь	0.22	_	0.38	0.009	_	0.015	
С	0.08	_	0.23	0.003		0.009	
E	4	.90 BS	C	0.193 BSC			
E1	3	5.00 BS	ic .	0.118 BSC			
е	(.65 BS	ic .	0.026 BSC			
e1	1	.95 BS	iC .	0.077 BSC			
L	0.40	0.60	0.80	0.016	0.024	0.031	
L1	().95 RE	F	0	.037 R	EF	
L2).25 BS	SC .	0	.010 B	SC	
R	0.07	_	_	0.003	_	_	
R1	0.07	_	_	0.003	-	_	
θ	0,	_	8*	0,	_	8*	
91	5*	_	15°	5*	_	15*	
D	3.00 BSC			C	.118 E	ISC	
N		8			8		

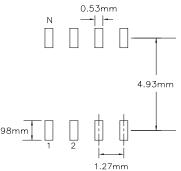


Front View

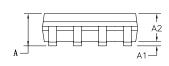
SOIC-8 Package



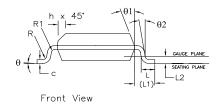






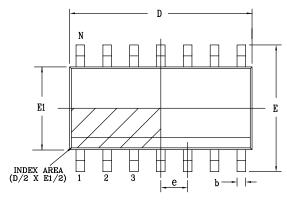


Side View

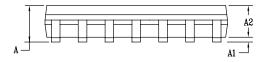


8 Pin	SOICN	JEDE	EC MS-	-012	Variatio	n AA
SYMBOLS		ISIONS II ontrol Un			SIONS IN rence Ur	
	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.35	_	1.75	0.053	l	0.069
A1	0.10	_	0.25	0.004	_	0.010
A2	1.25	_	1.65	0.049	_	0.065
b	0.31		0.51	0.012	_	0.020
С	0.17	_	0.25	0.007	_	0.010
Е	(5.00 BSC		0.236 BSC		
E1		3.90 BSC		0.154 BSC		
е		1.27 BSC		0.050 BSC		
h	0.25		0.50	0.010	_	0.020
L	0.40	_	1.27	0.016	_	0.050
L1		1.04 REF	7	0.041 REF		
L2	(0.25 BSC		0.	.010 BS	
R	0.07	_	_	0.003	_	_
R1	0.07	_	_	0.003	_	_
θ	0,	_	8°	0,	_	8*
θ1	5°		15°	5°	_	15°
θ2	0,	_	_	0,	_	_
D	4.90 BSC			0	.193 BS	2
N		8			8	

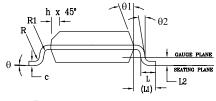
SOIC-14 Package



Top View



Side View

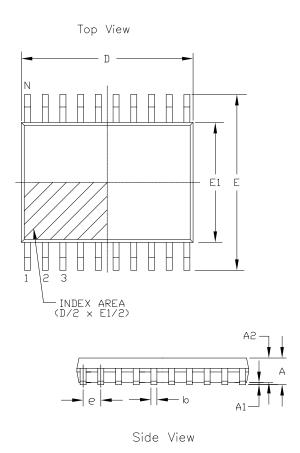


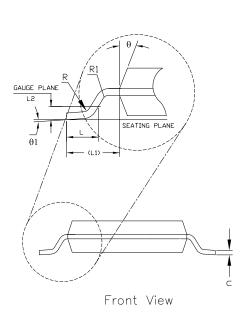
Front View

PACKAGE OUTLINE NSOIC .150" BODY JEDEC MS-012						
SYMBOLS		DIMENSION ontrol Unit)		COMMON DIMENSIONS IN IN (Reference Unit)		
	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.35	_	1.75	0.053	_	0.069
A1	0.10	_	0.25	0.004	_	0.010
A2	1.25	_	1.65	0.049		0.065
b	0.31	_	0.51	0.012		0.020
С	0.17	_	0.25	0.007		0.010
E	6.00 BSC 0.236 BSC					С
E1		3.90 BSC 0.154 BSC				С
е		1.27 BS0		0.050 BSC		
h	0.25	_	0.50	0.010	_	0.020
L	0.40	_	1.27	0.016	_	0.050
L1		1.04 REF	-	0	.041 REI	-
L2		0.25 BS0)	0	.010 BS	2
R	0.07	_	1	0.003	_	_
R1	0.07	_	_	0.003	_	_
θ	0,	_	8,	0,	_	8.
θ1	5*	_	15*	5*	_	15°
θ2	0,				_	_
D	SEE VARIATIONS					
N	I SEE VARIATIONS					
VARIATION						

	VARIATION D						
VARIATIONS	DIMENSIONS IN MM (Control Unit)				SIONS IN erence U		N
SNO	MIN NOM MAX		MIN	NOM	MAX		
AA	4	.90 BS	С	0	.193 BS	SC	8
AB	8.65 BSC			0	.341 B	SC	14
AC	9	.90 BS	С	0	.390 BS	SC	16

TSSOP-14 Package





14 Pin TSSOP JEDEC MO-153 Variation AB-1						
SYMBOLS		NSIONS ontrol U		DIMENSIONS IN INCH (Reference Unit)		
	MIN	NOM	MAX	MIN	NOM	MAX
Α	_	_	1.20	_	_	0.047
A1	0.05	_	0.15	0.002	_	0.006
A2	0.80	1.00	1.05	0.031	0.039	0.041
b	0.19	_	0.30	0.007	_	0.012
С	0.09	_	0.20	0.004	_	0.008
E	6	.40 BS	C	0.252 BSC		
E1	4.30	4.40	4.50	0.169	0.173	0.177
е	C	.65 BS	SC .	0.026 BSC		
L	0.45	0.60	0.75	0.018	0.024	0.030
L1		1.00 RE	F	0.039 REF		
L2	().25 BS	SC .	0	.010 B	SC
R	0.09	_	_	0.035	_	_
R1	0.09	_	_	0.035	—	—
θ	12° REF			-	2° RE	F
θ1	0,	_	8*	0,	_	8°
D	4.90	5.00	5.10	0.193	0.197	0.200
N		14			14	

Ordering Information

Part Number	Package	Green	Operating Temperature Range	Packaging				
CLC1007 Ordering Information	CLC1007 Ordering Information							
CLC1007IST5X*	TSOT-5	Yes	-40°C to +125°C	Tape & Reel				
CLC1007IST5MTR*	TSOT-5	Yes	-40°C to +125°C	Mini Tape & Reel				
CLC1007IST5EVB*	Evaluation Board	N/A	N/A	N/A				
CLC1007ISO8X	SOIC-8	Yes	-40°C to +125°C	Tape & Reel				
CLC1007ISO8MTR	SOIC-8	Yes	-40°C to +125°C	Mini Tape & Reel				
CLC1007ISO8EVB	Evaluation Board	N/A	N/A	N/A				
CLC2007 Ordering Information								
CLC2007ISO8X*	SOIC-8	Yes	-40°C to +125°C	Tape & Reel				
CLC2007ISO8MTR*	SOIC-8	Yes	-40°C to +125°C	Mini Tape & Reel				
CLC2007ISO8EVB*	Evaluation Board	N/A	N/A	N/A				
CLC2007IMP8X*	MSOP-8	Yes	-40°C to +125°C	Tape & Reel				
CLC2007IMP8MTR*	MSOP-8	SOP-8 Yes -40°0		Mini Tape & Reel				
CLC2007IMP8EVB*	Evaluation Board	N/A	N/A	N/A				
CLC4007 Ordering Information								
CLC4007ITP14X*	TSSOP-14	Yes	-40°C to +125°C	Tape & Reel				
CLC4007ITP14MTR*	TSSOP-14	Yes	-40°C to +125°C	Mini Tape & Reel				
CLC4007ITP14EVB*	Evaluation Board	N/A	N/A	N/A				
CLC4007ISO14X*	SOIC-14	Yes	-40°C to +125°C	Tape & Reel				
CLC4007ISO14MTR*	SOIC-14	Yes	-40°C to +125°C	Mini Tape & Reel				
CLC4007ISO14EVB*	Evaluation Board	N/A	N/A	N/A				

Moisture sensitivity level for all parts is MSL-1.

^{*}Contact Resurgent Semiconductor for availability.

Revision History

Revision	Date	Description
1D (ECN 1451-07)	December 2014	Reformat into Exar data sheet template. Updated ordering information table to include MTR and EVB part numbers. Increased "I" temperature range from +85 to +125°C. Removed "A" temp grade parts, since "I" is now equivalent. Updated thermal resistance numbers and package outline drawings.
1D.R	July 2018	Updated to Resurgent Semiconductor.

For Further Assistance:

www.resurgentsemi.net



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